

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

KOCHERGIN ET AL.

Serial No. 10/686,519

Filed: 16 October 2003



Atty. Ref.: 340-81

TC/A.U.: 2872

Examiner:

For: METHOD OF MANUFACTURING A SPECTRAL FILTER FOR
GREEN AND LONGER WAVELENGTHS

* * * * *

March 22, 2004

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

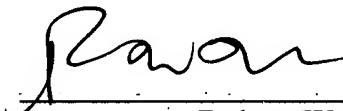
INFORMATION DISCLOSURE STATEMENT

In accordance with Rule 97, the undersigned attorney submits the documents listed on the attached form PTO-1449. A copy of each non-U.S. patent document is enclosed.

The Examiner is requested to initial the attached form PTO-1449 and to return a copy to the undersigned as an indication that the attached documents have been considered and made of record in this case.

Respectfully submitted,

NIXON & VANDERHYE P.C.

By: 

Robert W. Faris
Reg. No. 31,352

RWF:ejs
1100 North Glebe Road, 8th Floor
Arlington, VA 22201-4714
Telephone: (703) 816-4000
Facsimile: (703) 816-4100

**INFORMATION DISCLOSURE
CITATION**

ATTY. DOCKET NO.

SERIAL NO.

340-81

10/686,519

APPLICANT

KOCHERGIN ET AL.

(Use several sheets if necessary)

FILING DATE

TC/A.U.

16 October 2003

2872


U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	4,874,484	10/1989	Foell et al.			
	5,262,021	11/1993	V. Lehmann et al.			
	5,348,627	09/1994	Propst et al.			
	5,431,766	07/1995	Propst et al.			
	5,544,772	08/1996	Soave et al.			
	5,645,684	07/1997	Keller			
	5,987,208	11/1999	Grunig			
	5,997,713	12/1999	Beetz, Jr. et al.			
	6,521,149	02/2003	Mearini et al.			
	6,526,191	02/2003	Geusic et al.			

FOREIGN PATENT DOCUMENTS

DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
3717851		Germany			
4202454		Germany			

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

	Lehmann et al., Optical shortpass filters based on macroporous silicon <i>Appl. Phys. Lett.</i> V 78, N.5, Jan. 2001.
	J. Schilling et al., "Three-dimensional photonic crystals based on Macroporous silicon with modulated pore diameter", <i>Appl. Phys. Lett.</i> V 78, N.9, Feb. 2001
	S. Izuo et al., "A novel electrochemical etching technique for n-type silicon," <i>Sensors and Actuators A</i> 97-98 (2002), pp. 720-724
	A. Vyatkin et al., "Random and Ordered Macropore Formation in p-Type Silicon," <i>J. of the Electrochem. Soc.</i> , 149 (1), pp. G70-G76 (2002)
	H. Föll et. al, "Formation and application of porous silicon", <i>Mat. Sci. Eng. R</i> 39 (2002), pp.93-141
	S. Langa et al., "Observation of crossing pores in anodically etched n-GaAs," <i>Appl. Phys. Lett.</i> 78(8), pp.1074- 1076, (2001).
	H H. Föll et al., "Porous III-V compound semiconductors: formation, properties, and comparison to silicon", <i>Phys. Stat. Sol. A</i> , 197 (1), pp. 61-70 (2003)
	M. Christophersen et al., "A comparison of pores in silicon and pores in III-V compound materials", <i>Phys. Stat. Sol. A</i> , 197 (1), pp. 197-203, (2003)
	H. Föll et al., "Pores in III-V Semiconductors", <i>Adv. Materials, Review</i> , 2003, 15, pp.183 - 198, (2003)
	S. Langa et al., <i>Phys. Stat. Sol. A</i> , 197 (1), p. 77, (2003) "Single crystalline 2D porous arrays obtained by self organization in n-InP" (pp. 77-82)

*Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.